

PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1
 Stylesheet Version v1.2

EPAS ID: PAT6400444

SUBMISSION TYPE:	NEW ASSIGNMENT	
NATURE OF CONVEYANCE:	ASSIGNMENT	
CONVEYING PARTY DATA		
	Name	Execution Date
	SORAA, INC.	09/08/2017
RECEIVING PARTY DATA		
Name:	SLT TECHNOLOGIES, INC	
Street Address:	C/O LOEB & LOEB	
Internal Address:	10100 SANTA MONICA BLVD., SUITE 2200	
City:	LOS ANGELES	
State/Country:	CALIFORNIA	
Postal Code:	90067	
PROPERTY NUMBERS Total: 1		
	Property Type	Number
	Application Number:	16868528
CORRESPONDENCE DATA		
Fax Number:	(713)623-4846	
<i>Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.</i>		
Phone:	7136234844	
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Correspondent Name:	PATTERSON & SHERIDAN, LLP	
Address Line 1:	24 GREENWAY PLAZA	
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ATTORNEY DOCKET NUMBER:	SLTC_0066USC01 ASG 2	
NAME OF SUBMITTER:	JOSEPH J. STEVENS	
SIGNATURE:	/Joseph J. Stevens/	
DATE SIGNED:	11/13/2020	
Total Attachments: 9		
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PATENT ASSIGNMENT AGREEMENT

This PATENT ASSIGNMENT AGREEMENT ("**Patent Assignment**"), dated as of September 22, is made by Soraa, Inc. ("**Seller**"), a Delaware corporation, in favor of SLT Technologies, Inc. ("**Buyer**"), a Delaware corporation, the purchaser of certain assets of Seller pursuant to an Asset Purchase Agreement dated as of September 8, 2017 (the "**Asset Purchase Agreement**").

WHEREAS, under the terms of the Asset Purchase Agreement, Seller has agreed to sell, convey, transfer, assign, and deliver to Buyer, among other assets, certain patents and patent applications of Seller, and has agreed to execute and deliver this Patent Assignment, for the purpose of recording the assignment with the United States Patent and Trademark Office and the corresponding patent offices, entities or agencies in any applicable jurisdiction (including any applicable foreign country);

NOW THEREFORE, in accordance with the Asset Purchase Agreement and in consideration of the promises and covenants contained herein and therein, the parties agree as follows:

1. Assignment. For good and valuable consideration, the receipt and sufficiency of which are hereby acknowledged, Seller hereby irrevocably sells, conveys, transfers, assigns, and delivers to Buyer, and Buyer hereby accepts, all of Seller's right, title, and interest in and to the following (the "**Assigned Patents**"):

(a) the patents and patent applications set forth in Schedule 1 hereto and all issuances, divisions, continuations, continuations-in-part, reissues, extensions, reexaminations, and renewals thereof;

(b) all rights of Seller accruing under any of the foregoing provided by applicable law of any jurisdiction, by international treaties and conventions, and otherwise throughout the world;

(c) any and all royalties, fees, income, payments, and other proceeds now or hereafter due or payable with respect to any and all of the foregoing; and

(d) any and all claims and causes of action based on any of the foregoing, whether accruing before, on, or after the date hereof, including all rights to and claims for damages, restitution, and injunctive and other legal and equitable relief for past, present, and future infringement, misappropriation, violation, misuse, breach, or default, with the right but no obligation to sue for such legal and equitable relief and to collect, or otherwise recover, any such damages.

2. Recordation and Further Actions. Seller hereby authorizes the Commissioner for Patents in the United States Patent and Trademark Office and the officials of corresponding patent offices, entities or agencies in any applicable jurisdiction (including any applicable foreign country) to record and register this Patent Assignment upon request by Buyer. Following the date hereof, upon Buyer's reasonable request, Seller shall take such reasonable steps and actions, and provide such reasonable cooperation and assistance to Buyer and its successors, assigns, and legal representatives, including the execution and delivery of any affidavits, declarations, oaths, exhibits, assignments, powers of attorney, or other documents, as may be reasonably necessary to effect, evidence, or perfect the assignment of the Assigned Patents to Buyer, or any assignee or successor thereto.

3. Terms of the Asset Purchase Agreement. The parties hereto acknowledge and agree that this Patent

Assignment is entered into pursuant to the Asset Purchase Agreement, to which reference is made for a further statement of the rights and obligations of Seller and Buyer with respect to the Assigned Patents. The representations, warranties, covenants, agreements, and indemnities contained in the Asset Purchase Agreement shall not be superseded hereby but shall remain in full force and effect to the full extent provided therein. In the event of any conflict or inconsistency between the terms of the Asset Purchase Agreement and the terms hereof, the terms of the Asset Purchase Agreement shall govern.

4. Counterparts. This Patent Assignment may be executed in counterparts, each of which shall be deemed an original, but all of which together shall be deemed one and the same agreement. A signed copy of this Patent Assignment delivered by facsimile, e-mail, or other means of electronic transmission shall be deemed to have the same legal effect as delivery of an original signed copy of this Patent Assignment.

5. Successors and Assigns. This Patent Assignment shall be binding upon and shall inure to the benefit of the parties hereto and their respective successors and assigns.

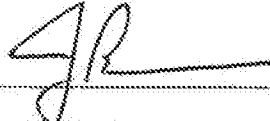
6. Governing Law. This Patent Assignment shall be governed by, and construed and enforced in accordance with, the laws of the State of California other than conflict of laws principles thereof directing the application of any law other than that of California.

7. Entire Agreement. This Patent Assignment and the Schedule attached hereto, together with the Asset Purchase Agreement, constitute the entire agreement between the parties with respect to the subject matter of this Patent Assignment and supersede all prior agreements and understandings, both oral and written, between the parties with respect to the subject matter of this Patent Assignment.

[Signature page follows]

IN WITNESS WHEREOF, the parties have duly executed and delivered this Patent Assignment as of the date first above written.

SORAA, INC.

By: 

Name: Jeff Parker

Title: Chief Executive Officer

Address for Notices:

6500 Kaiser Drive, Suite 110
Fremont, CA 94555

SLT TECHNOLOGIES, INC.

By: _____

Name: Kenneth Benbassat

Title: Secretary

Address for Notices:

c/o Loeb & Loeb LLP
10100 Santa Monica Blvd., Suite 2200
Los Angeles, CA 90067

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[SIGNATURE PAGE TO PATENT ASSIGNMENT]

PATENT
REEL: 054361 FRAME: 0006

SCHEDULE 1
ASSIGNED PATENTS

TITLE	COUNTRY	STATUS	APPLN. NO.	FILING DATE	PATENT NO.	ISSUE DATE
HIGH PRESSURE APPARATUS AND METHOD FOR NITRIDE CRYSTAL GROWTH	USA	Issued	12/133,364	6/5/2008	8,097,081	1/17/2012
HIGH PRESSURE APPARATUS AND METHOD FOR NITRIDE CRYSTAL GROWTH	USA	Issued	13/013,697	1/25/2011	8,871,024	10/28/2014
HIGH PRESSURE APPARATUS AND METHOD FOR NITRIDE CRYSTAL GROWTH	USA	Issued	13/343,563	1/4/2012	8,986,447	3/24/2015
HIGH PRESSURE APPARATUS AND METHOD FOR NITRIDE CRYSTAL GROWTH	Japan	Issued	2011-512644	6/4/2009	5536046	5/9/2014
HIGH PRESSURE APPARATUS AND METHOD FOR NITRIDE CRYSTAL GROWTH	USA	Issued	12/478,736	6/4/2009	8,303,710	11/6/2012
HIGH PRESSURE APPARATUS AND METHOD FOR NITRIDE CRYSTAL GROWTH	Japan	Issued	2014-088867	6/4/2009	6138724	5/12/2017
HIGH PRESSURE APPARATUS AND METHOD FOR NITRIDE CRYSTAL GROWTH	USA	Issued	13/556,105	7/23/2012	9,157,167	10/13/2015
PROCESS FOR LARGE-SCALE AMMONOTHERMAL MANUFACTURING OF GALLIUM NITRIDE BOULES	USA	Issued	12/534,844	8/3/2009	8,979,999	3/17/2015
PROCESS FOR LARGE-SCALE AMMONOTHERMAL MANUFACTURING OF GALLIUM NITRIDE BOULES	USA	Rejected	14/599,335	1/16/2015		
APPARATUS AND METHOD FOR SEED CRYSTAL UTILIZATION IN LARGE-SCALE MANUFACTURING OF GALLIUM NITRIDE	USA	Issued	12/534,843	8/3/2009	8,430,958	4/30/2013
PROCESS AND APPARATUS FOR LARGE-SCALE MANUFACTURING OF BULK MONOCRYSTALLINE GALLIUM-CONTAINING NITRIDE	USA	Issued	12/534,857	8/4/2009	8,021,481	9/20/2011
PROCESS AND APPARATUS FOR LARGE-SCALE MANUFACTURING OF BULK MONOCRYSTALLINE GALLIUM-CONTAINING NITRIDE	USA	Issued	13/226,249	9/6/2011	8,444,765	5/21/2013
PROCESS AND APPARATUS FOR GROWING A CRYSTALLINE GALLIUM-CONTAINING NITRIDE USING AN AZIDE MINERALIZER	USA	Issued	12/534,849	8/3/2009	8,323,405	12/4/2012
NITRIDE CRYSTAL WITH REMOVABLE SURFACE LAYER AND METHODS OF MANUFACTURE	USA	Issued	12/546,458	8/24/2009	8,148,801	4/3/2012
NITRIDE CRYSTAL WITH REMOVABLE SURFACE LAYER AND METHODS OF MANUFACTURE	USA	Issued	13/425,304	3/20/2012	8,329,511	12/11/2012
LARGE-AREA SEED FOR AMMONOTHERMAL GROWTH OF BULK GALLIUM NITRIDE AND METHOD OF MANUFACTURE	USA	Issued	12/556,558	9/9/2009	7,976,630	7/12/2011
AMMONOTHERMAL METHOD FOR GROWTH OF BULK GALLIUM NITRIDE	USA	Issued	13/175,739	7/1/2011	8,465,588	6/18/2013
POLYCRYSTALLINE GROUP III METAL NITRIDE WITH GETTER AND METHOD OF MAKING	China	Issued	200980154756.9	12/11/2009	200980154756.9	5/13/2015
POLYCRYSTALLINE GROUP III METAL NITRIDE WITH GETTER AND METHOD OF MAKING	Japan	Issued	2011-540937	12/11/2009	5476637	2/21/2014
POLYCRYSTALLINE GROUP III METAL NITRIDE WITH GETTER AND METHOD OF MAKING	USA	Issued	12/634,665	12/9/2009	8,461,071	6/11/2013

POLYCRYSTALLINE GROUP III METAL NITRIDE WITH GETTER AND METHOD OF MAKING	USA	Issued	13/894,220	5/14/2013	8,987,156	3/24/2015
POLYCRYSTALLINE GROUP III METAL NITRIDE WITH GETTER AND METHOD OF MAKING	USA	Pending	15/469,196	3/24/2017		
LARGE-AREA BULK GALLIUM NITRIDE WAFER AND METHOD OF MANUFACTURE	USA	Issued	12/556,562	9/9/2009	8,048,225	11/1/2011
HIGH PRESSURE APPARATUS WITH STACKABLE RINGS	USA	Issued	12/891,668	9/27/2010	8,435,347	5/7/2013
METHOD FOR SYNTHESIS OF HIGH QUALITY LARGE AREA BULK GALLIUM BASED CRYSTALS	USA	Issued	12/988,772	6/30/2011	9,175,418	11/3/2015
METHOD FOR SYNTHESIS OF HIGH QUALITY LARGE AREA BULK GALLIUM BASED CRYSTALS	USA	Pending	14/930,170	11/2/2015		
IMPROVED SEMI-INSULATING GROUP III METAL NITRIDE AND METHOD OF MANUFACTURE	China	Pending	201110061625.5	3/11/2011		
SEMI-INSULATING GROUP III METAL NITRIDE AND METHOD OF MANUFACTURE	USA	Issued	13/041,199	3/4/2011	8,878,230	11/4/2014
APPARATUS FOR LARGE VOLUME AMMONOTHERMAL MANUFACTURE OF GALLIUM NITRIDE CRYSTALS AND METHODS OF USE	USA	Issued	13/656,615	10/19/2012	9,724,666	8/8/2017
APPARATUS FOR LARGE VOLUME AMMONOTHERMAL MANUFACTURE OF GALLIUM NITRIDE CRYSTALS AND METHODS OF USE	USA	Pending	15/474,806	3/30/2017		
APPARATUS FOR LARGE VOLUME AMMONOTHERMAL MANUFACTURE OF GALLIUM NITRIDE CRYSTALS AND METHODS OF USE	USA	Pending	13/657,551	10/22/2012		
PROCESS FOR LARGE-SCALE AMMONOTHERMAL MANUFACTURING OF SEMIPOLAR GALLIUM NITRIDE BOULES	Japan	Issued	2013-117510	6/4/2013	5788433	8/7/2015
PROCESS FOR LARGE-SCALE AMMONOTHERMAL MANUFACTURING OF SEMIPOLAR GALLIUM NITRIDE BOULES	USA	Pending	13/908,836	6/3/2013		
ULTRAPURE MINERALIZERS AND METHODS FOR NITRIDE CRYSTAL GROWTH	USA	Issued	14/033,107	9/20/2013	9,299,555	3/29/2016
ULTRAPURE MINERALIZERS AND METHODS FOR NITRIDE CRYSTAL GROWTH	Japan	Pending	2016-044917	3/8/2016		
LARGE AREA, LOW-DEFECT GALLIUM-CONTAINING NITRIDE CRYSTALS, METHOD OF MAKING, AND METHOD OF USE	USA	Issued	13/600,191	8/30/2012	9,404,197	8/2/2016
LARGE AREA, LOW-DEFECT GALLIUM-CONTAINING NITRIDE CRYSTALS, METHOD OF MAKING, AND METHOD OF USE	USA	Pending	15/226,552	8/2/2016		
METHOD FOR QUANTIFICATION OF EXTENDED DEFECTS IN GALLIUM-CONTAINING NITRIDE CRYSTALS	USA	Issued	14/013,753	8/29/2013	9,275,912	3/1/2016
HIGH QUALITY GROUP-III METAL NITRIDE CRYSTALS, METHODS OF MAKING, AND METHODS OF USE	Japan	Pending	2013-243510	11/26/2013		
HIGH QUALITY GROUP-III METAL NITRIDE CRYSTALS, METHODS OF MAKING, AND METHODS OF USE	USA	Issued	14/089,281	11/25/2013	9589792	03/07/2017
LARGE AREA SEED CRYSTAL FOR AMMONOTHERMAL CRYSTAL GROWTH AND METHOD OF MAKING	USA	Issued	14/249,708	4/10/2014	9650723	05/16/2017

TRANSPARENT GROUP III METAL NITRIDE AND METHOD OF MANUFACTURE	USA	Issued	14/485,516	9/12/2014	9543392	01/10/2017
REUSABLE NITRIDE WAFER, METHOD OF MAKING, AND METHOD OF USE	USA	Issued	14/805,278	7/21/2015	9653554	05/16/2017
REUSABLE NITRIDE WAFER, METHOD OF MAKING, AND USE THEREOF	USA	Pending	15/596,728	5/16/2017		
METHOD AND SYSTEM FOR PREPARING POLYCRYSTALLINE GROUP III METAL NITRIDE	USA	Pending	15/011,266	1/29/2016		
PRESSURE RELEASE MECHANISM FOR CAPSULE AND METHOD OF USE WITH SUPERCRITICAL FLUIDS	USA	Pending	15/269,538	9/19/16		
PRESSURE VESSEL	JAPAN	Issued	2003-563702	11/22/2002	4451662	2/5/2010
IMPROVED PRESSURE VESSEL	GERMANY	Issued	DE2002614436	11/22/2002	60214436	10/12/2006
IMPROVED PRESSURE VESSEL	FRANCE	Issued	2789868.3	11/22/2002	1476249	8/30/2006
HIGH TEMPERATURE HIGH PRESSURE CAPSULE FOR PROCESSING MATERIALS IN SUPERCRITICAL FLUIDS	USA	Issued	09/683659	1/31/2002	7,125,453	10/24/2006
HIGH TEMPERATURE HIGH PRESSURE CAPSULE FOR PROCESSING MATERIALS IN SUPERCRITICAL FLUIDS	USA	Issued	11/010139	12/10/2004	7,625,446	12/1/2009
CRYSTALLINE COMPOSITION, DEVICE, AND ASSOCIATED METHOD	USA	Issued	11/313451	12/20/2005	8,039,412	10/18/2011
APPARATUS FOR MAKING CRYSTALLINE COMPOSITION	USA	Issued	11/313442	12/20/2005	7,942,970	5/17/2011
METHOD FOR MAKING CRYSTALLINE COMPOSITION	USA	Issued	11/313528	12/20/2005	7,935,382	5/3/2011
CRYSTALLINE COMPOSITION, DEVICE, AND ASSOCIATED METHOD	CHINA	Issued	200680053099.5	12/15/2006	101379227	6/12/2013
CRYSTALLINE COMPOSITION, DEVICE, AND ASSOCIATED METHOD	EUROPE	Pending	06845438.8	12/15/2006		
CRYSTALLINE COMPOSITION, DEVICE, AND ASSOCIATED METHOD	JAPAN	Issued	2008-547331	12/20/2005	5143016	2/13/2013
CRYSTALLINE COMPOSITION, DEVICE, AND ASSOCIATED METHOD	KOREA (SOUTH)	Issued	2008-7015178	12/20/2005	101351498	1/15/2014
CRYSTALLINE GALLIUM NITRIDE AND METHOD FOR FORMING CRYSTALLINE GALLIUM NITRIDE	USA	Issued	09/413446	10/6/1999	6,398,867	6/4/2002
CRYSTALLINE GALLIUM NITRIDE AND METHOD FOR FORMING CRYSTALLINE GALLIUM NITRIDE	FRANCE	Issued	967039.9	9/28/2000	1230005	1/3/2007
CRYSTALLINE GALLIUM NITRIDE AND METHOD FOR FORMING CRYSTALLINE GALLIUM NITRIDE	GERMANY	Issued	967039.9	9/28/2000	60032793	2/15/2007
CRYSTALLINE GALLIUM NITRIDE AND METHOD FOR FORMING CRYSTALLINE GALLIUM NITRIDE	NETHERLANDS	Issued	967039.9	9/28/2000	1230005	1/3/2007
CRYSTALLINE GALLIUM NITRIDE AND METHOD FOR FORMING CRYSTALLINE GALLIUM NITRIDE	JAPAN	Issued	2001-527911	9/28/2000	4942270	5/30/2012
CRYSTALLINE GALLIUM NITRIDE AND METHOD FOR FORMING CRYSTALLINE GALLIUM NITRIDE	KOREA (SOUTH)	Issued	10-2002-7004411	9/28/2000	10-07620190000	6/19/2007
HIGH PRESSURE/HIGH TEMPERATURE APPARATUS WITH IMPROVED TEMPERATURE CONTROL FOR CRYSTAL GROWTH	USA	Issued	10/699504	10/31/2003	7,101,433	9/5/2006
HIGH PRESSURE HIGH TEMPERATURE GROWTH OF CRYSTALLINE GROUP III METAL NITRIDES	USA	Issued	10/063164	3/27/2002	7,063,741	6/20/2006

HIGH PRESSURE HIGH TEMPERATURE GROWTH OF CRYSTALLINE GROUP III METAL NITRIDES	GERMANY	Issued	3709199.8	2/21/2003	EP1490537 / DE603367 15	4/13/2011
HIGH PRESSURE HIGH TEMPERATURE GROWTH OF CRYSTALLINE GROUP III METAL NITRIDES	KOREA (SOUTH)	Issued	20047015545	2/21/2003	100987850	10/13/2010
APPARATUS FOR PRODUCING SINGLE CRYSTAL AND QUASI-SINGLE CRYSTAL, AND ASSOCIATED METHOD	USA	Issued	11/249896	10/13/2005	7,368,015	5/6/2008
APPARATUS FOR PROCESSING MATERIALS IN SUPERCRITICAL FLUIDS AND METHODS THEREOF	USA	Issued	11/042858	1/25/2005	7,704,324	4/27/2010
IMPROVED APPARATUS FOR HIGH TEMPERATURE HIGH PRESSURE PROCESSING	RUSSIAN FEDERAT	Issued	2007132167	10/19/2005	2393008	6/27/2010
IMPROVED APPARATUS FOR HIGH TEMPERATURE HIGH PRESSURE PROCESSING	POLAND	Issued	EP05811853	10/19/2005	1846148	12/22/2010
IMPROVED APPARATUS FOR HIGH TEMPERATURE HIGH PRESSURE PROCESSING	NETHERLANDS	Issued	EP05811853	10/19/2005	1846148	12/22/2010
IMPROVED APPARATUS FOR HIGH TEMPERATURE HIGH PRESSURE PROCESSING	GERMANY	Issued	EP05811853	10/19/2005	602005025 533	2/3/2011
IMPROVED APPARATUS FOR HIGH TEMPERATURE HIGH PRESSURE PROCESSING	FRANCE	Issued	EP05811853	10/19/2005	1846148	12/22/2010
APPARATUS FOR PROCESSING MATERIALS IN SUPERCRITICAL FLUIDS	EUROPE	Pending	EP20100011809	10/19/2005		
IMPROVED APPARATUS FOR HIGH TEMPERATURE HIGH PRESSURE PROCESSING	CHINA	Issued	200580047233.6	10/19/2005	101163540	4/13/2011
HEATER, APPARATUS, AND ASSOCIATED METHOD	USA	Issued	11/521034	9/14/2006	7,705,276	4/27/2010
INCOMPRESSIBLE HEATER AND METHOD FOR MAKING	CHINA	Issued	200610064789.2	11/30/2006	101146379	11/9/2011
INCOMPRESSIBLE HEATER AND METHOD FOR MAKING	FRANCE	Issued	EP06024819	11/30/2006	EP1901584	30/5/2016
INCOMPRESSIBLE HEATER AND METHOD FOR MAKING	POLAND	Issued	EP06024819	11/30/2006	EP1901584	30/5/2016
HEATER, APPARATUS, AND ASSOCIATED METHOD	JAPAN	Issued	2006-323731	11/30/2006	5044202	10/10/2012
HEATER, APPARATUS, AND ASSOCIATED METHOD	KOREA (SOUTH)	Issued	20060120252	11/30/2006	101310437	9/25/2013
METHOD FOR FORMING NITRIDE CRYSTALS	USA	Issued	11/973182	10/5/2007	7,642,122	1/5/2010
METHOD FOR FORMING NITRIDE CRYSTALS	JAPAN	Issued	2009-531469	10/5/2007	5480624	4/23/2014
METHOD FOR FORMING NITRIDE CRYSTALS	EUROPE	Granted	07852559.9	10/5/2007		
ETCHANT, METHOD OF ETCHING, LAMINATE FORMED THEREBY, AND DEVICE	USA	Issued	11/167719	6/27/2005	7,527,742	5/5/2009
SINTERED POLYCRYSTALLINE GALLIUM NITRIDE AND ITS PRODUCTION	USA	Issued	10/001575	11/2/2001	6,861,130	3/1/2005
SINTERED POLYCRYSTALLINE GALLIUM NITRIDE	JAPAN	Issued	2003-543080	10/30/2002	4349907	10/21/2009
SINTERED POLYCRYSTALLINE GALLIUM NITRIDE	CHINA	Issued	2821830.2	10/30/2002	1280182	10/18/2006
SINTERED POLYCRYSTALLINE GALLIUM NITRIDE	KOREA (SOUTH)	Issued	10-2004-7006467	4/29/2004	10-090325 1	6/9/2009
APPARATUS FOR PROCESSING MATERIALS AT HIGH TEMPERATURES AND PRESSURES	USA	Pending	13/812757	7/28/2011		

APPARATUS FOR PROCESSING MATERIALS AT HIGH TEMPERATURES AND PRESSURES	JAPAN	Issued	2013521972	7/28/2011	5887344	2/19/2016
TRANSISTOR PATENT: HOMOEPIITAXIAL GALLIUM-NITRIDE-BASED ELECTRONIC DEVICES AND METHOD FOR PRODUCING SAME	USA	Issued	10/329982	12/27/2002	8089097	01/03/2012